

# GaAs INTEGRATED CIRCUIT $\mu$ PG2134TB

#### L-BAND PA DRIVER AMPLIFIER

#### **DESCRIPTION**

The  $\mu$ PG2134TB is GaAs MMIC for PA driver amplifier which were developed for mobile phone and another L-band application.

This device can operate with 3.0 V TYP., having the high gain and low distortion. This device is housed in a 6-pin super minimold package. And this package is able to high-density surface mounting.

#### **FEATURES**

Operation frequency : f<sub>opt</sub> = 1 429 to 1 453 MHz (1 441 MHz TYP.)

• Supply voltage : V<sub>DD1</sub> = 2.7 to 3.3 V (3.0 V TYP.)

:  $V_{DD2} = 2.7$  to 4.2 V (3.5 V TYP.)

Circuit current : Idd = 28 mA TYP. @ Vdd1 = 3.0 V, Vdd2 = 3.5 V, Vagc = 2.5 V, Pin = -15 dBm
 Power gain : GP = 28 dB TYP. @ Vdd1 = 3.0 V, Vdd2 = 3.5 V, Vagc = 2.5 V, Pin = -15 dBm

Gain control range
 GCR = 42 dB TYP. @ Vdd1 = 3.0 V, Vdd2 = 3.5 V, Vagc = 0.5 to 2.5 V,

 $P_{in} = -15 \text{ dBm}$ 

Low distortion
 Padj1 = -60 dBc TYP. @ VDD1 = 3.0 V, VDD2 = 3.5 V, VAGC = 2.5 V, Pout = +10 dBm,

 $f = 1 441 \text{ MHz}, \Delta f = \pm 50 \text{ kHz}, 21 \text{ kHz Bandwidth}$ 

High-density surface mounting: 6-pin super minimold package (2.0 × 1.25 × 0.9 mm)

#### **APPLICATION**

· Digital Cellular: PDC 1.5 GHz etc.

#### ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPG2134TB-E3	6-pin super minimold	G3B	<ul> <li>Embossed tape 8 mm wide</li> <li>Pin 1, 2, 3 face the perforation side of the tape</li> <li>Qty 3 kpcs/reel</li> </ul>

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: μPG2134TB

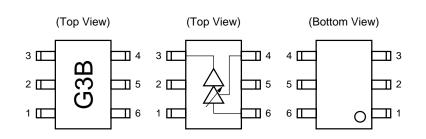
Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

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#### PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	V <sub>DD1</sub>
2	GND
3	OUTPUT/V <sub>DD2</sub>
4	Vagc
5	GND
6	INPUT

### ABSOLUTE MAXIMUM RATINGS (Ta = +25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Supply Voltage1, 2	V <sub>DD1, 2</sub>	6.0	V
Gain Control Voltage	Vagc	6.0	V
Input Power	Pin	-8	dBm
Power Dissipation	P□	140 Note	mW
Operating Ambient Temperature	TA	−30 to +90	°C
Storage Temperature	Tstg	−35 to +150	°C

**Note** Mounted on double-sided copper-clad  $50 \times 50 \times 1.6$  mm epoxy glass PWB, T<sub>A</sub> = +85°C

## RECOMMENDED OPERATING RENGE (TA = +25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Operating Frequency	f <sub>opt</sub>	1 429	1 441	1 453	MHz
Supply Voltage1	V <sub>DD1</sub>	2.7	3.0	3.3	<b>V</b>
Supply Voltage2	V <sub>DD2</sub>	2.7	3.5	4.2	<b>V</b>
Gain Control Voltage	Vagc	0	-	2.5	V
Input Power	Pin	-	-15	-10	dBm

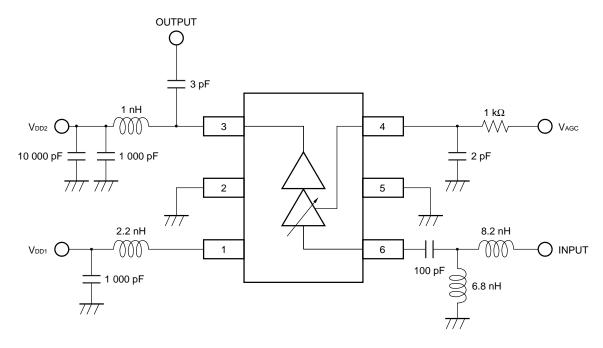
#### **ELECTRICAL CHARACTERISTICS**

(TA = +25°C, VDD1 = 3.0 V, VDD2 = 3.5 V,  $\pi$ /4DQPSK modulated signal input, with external input and output matching, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency	f <sub>opt</sub>		1 429	1 441	1 453	MHz
Circuit Current	IDD	Pin = -15 dBm, VAGC = 2.5 V	-	28	35	mA
Power Gain	G₽	Pin = -15 dBm, VAGC = 2.5 V	26	28	-	dB
Adjacent Channel Power Leakage 1	P <sub>adj1</sub>	$P_{out} = +10 \text{ dBm}, V_{AGC} = 2.5 \text{ V},$ $\Delta f = \pm 50 \text{ kHz}, 21 \text{ kHz Bandwidth}$	-	-60	-55	dBc
Adjacent Channel Power Leakage 2	P <sub>adj2</sub>	Pout = +10 dBm, V <sub>AGC</sub> = 2.5 V, $\Delta f = \pm 100$ kHz, 21 kHz Bandwidth	-	-70	-65	dBc
Gain Control Range	GCR	$P_{in} = -15 \text{ dBm}, V_{AGC} = 0.5 \text{ to } 2.5 \text{ V}$	37	42	-	dB
Gain Control Current	IAGC	V <sub>AGC</sub> = 0.5 to 2.5 V	-	1	20	μΑ

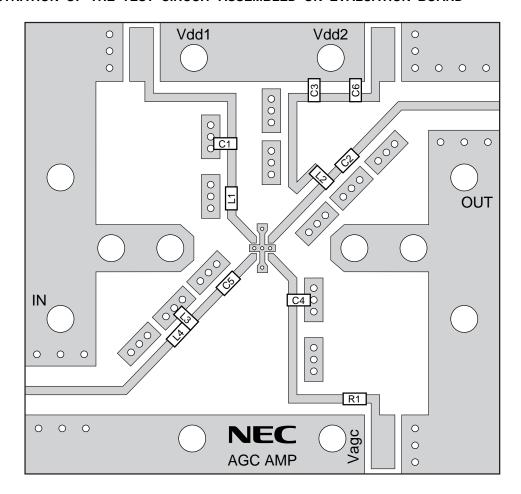
#### **EVALUATION CIRCUIT**

 $f = 1 441 \text{ MHz}, V_{DD1} = 3.0 \text{ V}, V_{DD2} = 3.5 \text{ V}$ 



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

#### ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

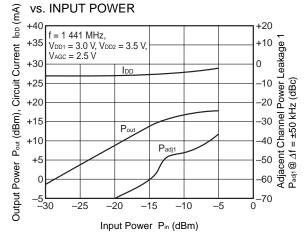


#### USING THE NEC EVALUATION BOARD

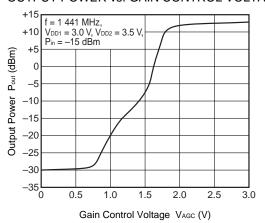
Symbol	Values	Part Number	Maker
C1, C3	1 000 pF	GRM39CH102J25PB	muRata
C2	3 pF	GRM39CH030C50PB	muRata
C4	2 pF	GRM39CH020C50PB	muRata
C5	100 pF	GRM39CH101J50PB	muRata
C6	10 000 pF	GRM39CH103J25PB	muRata
L1	2.2 nH	TFL0816-2N7	Susumu
L2	1.0 nH	TFL0816-1N0	Susumu
L3	6.8 nH	TFL0816-6N8	Susumu
L4	8.2 nH	TFL0816-8N2	Susumu
R1	1 kΩ	RR0816P-102-D	Susumu

#### TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

# OUTPUT POWER, CIRCUIT CURRENT, ADJACENT CHANNEL POWER LEAKAGE



#### OUTPUT POWER vs. GAIN CONTROL VOLTAGE

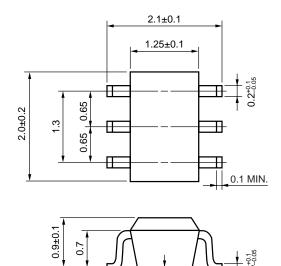


Remark The graphs indicate nominal characteristics.

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#### **PACKAGE DIMENSIONS**

# 6-PIN SUPER MINIMOLD (UNIT: mm)



0 to 0.1

#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol	
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	W\$260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

NEC  $\mu$ PG2134TB

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